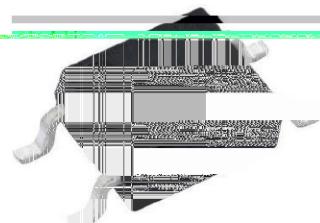


## 1. Features

- Current transfer ratio(CTR : MIN. 50% at  $I_F = 5\text{mA}$ ,  $V_{CE} = 5\text{V}$ ,  $T_a=25^\circ\text{C}$ )
- High input -output isolation voltage (  $V_{iso}=3,750\text{Vrms}$  )
- High collector-emitter voltage (  $V_{CEO} = 80\text{V}$  )
- SOP-4 package
- $\text{ESD} > 20\text{kV}$



b. Cross section view [Search standards](#)

### 2. Applications

- The infrared source device consists of an infrared led, photo transistor detector.
- Low ESD protection in
- Pin pitch of OR-357 is 2.54mm
- The bridged emitter will require high density mounting.

Internal  
Diagram

## 3. Main Performance Rated Values (Refer to Fig.1)

A. Main Dimensions

1	$I_F$	5	$V_{CE}$	5	$P_{on}$	150	$mW$
2	Reverse $V_B$ Voltage	5	$I_{CO}$	<10	$V_{BE(on)}$	~0.6	$mV$
3	$H_F$	100	$V_{CE(sat)}$	~1.5	$I_{BO}$	~100	$\mu A$
4	Collector-emitter Voltage	$V_C$	$I_{BO}$	~100	$I_{CBO}$	~100	$\mu A$
5	$V_R$	5	$P_{on}$	150	$V_{BR}$	80	$V$
6	Consume Power	$P_o$					
7	Reverse Power	$P_R$					
8	% Ince	$\Delta I_F$					
9	Breakdown	$V_{BR}$					
10	Isolation	$V_{iso}$					
11	Structure	$S$					



